



## ROTOR DIODE D105-630X

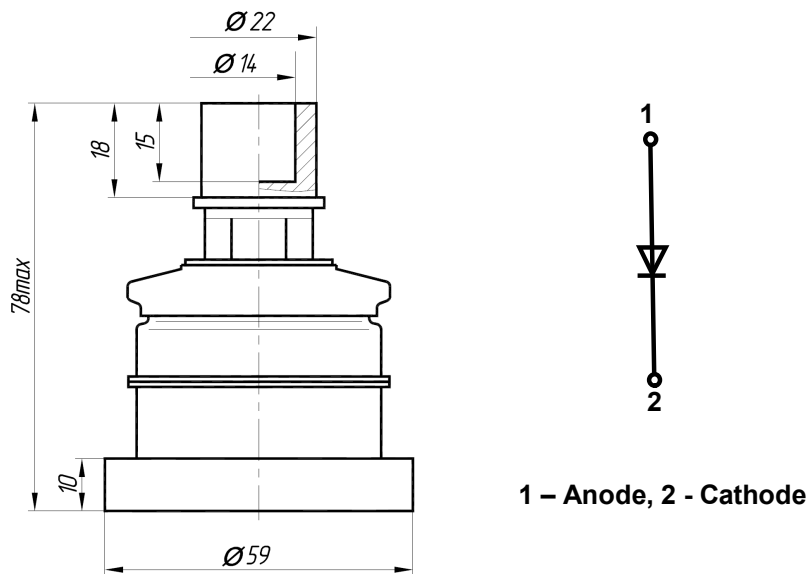
<ul style="list-style-type: none"> <li>◆ <math>V_{RRM} = \underline{2000-2800\text{ V}}</math></li> <li>◆ <math>I_{F(AV)} = \underline{630\text{ A}}</math> (<math>T_C = 100^\circ\text{C}</math>)</li> <li>◆ <math>I_{FSM} = \underline{15\text{ kA}}</math> (<math>t_p = 10\text{ms}</math>)</li> </ul>			
<ul style="list-style-type: none"> <li>◆ Flange design (terminals – round copper flange (base plate) and copper pipe)</li> <li>◆ By means of special arrangement centrifugal forces are applied not to silicon chip but to case, providing safe operation in large mechanical force conditions</li> </ul>			
<b>MAXIMUM RATED VALUES</b>			
Parameter and conditions	Symbol	Values	Units
Repetitive peak reverse voltage, $T_j = -60 \dots + 175\text{ }^\circ\text{C}$	$V_{RRM}$	2000-2800	V
Non- repetitive peak reverse voltage, $T_j = -60 \dots + 175\text{ }^\circ\text{C}$	$V_{RSM}$	2100-2900	
Repetitive peak reverse current, $T_j = 175\text{ }^\circ\text{C}$ , $V_R = V_{RRM}$	$I_{RRM}$	50	mA
Maximum average forward current, $T_C = 100\text{ }^\circ\text{C}$ , $f = 50\text{ Hz}$	$I_{F(AV)}$	630	A
RMS forward current, $T_C = 100\text{ }^\circ\text{C}$ , $f = 50\text{ Hz}$	$I_{FRMS}$	989	
Surge non-repetitive current, $T_j = 175\text{ }^\circ\text{C}$ , $V_R = 0$ , $t_p = 10\text{ ms}$	$I_{FSM}$	15	kA
Safety factor	$I^2t$	$1125 \cdot 10^3$	$\text{A}^2\text{s}$
Operation junction temperature range	$T_j$	-60 ... +175	°C
Storage temperature range	$T_{stg}$	-60 ... +50	

**D105-630X**

<b>ELECTRICAL CHARACTERISTICS</b>					
Parameter and conditions	Symbol	Values			Units
		min	typ.	max	
Maximum peak forward voltage, $T_j = 25\text{ °C}, I_F = 1980\text{ A}$	$V_{FM}$	-	-	1,6	V
On-state threshold voltage, $T_j = 175\text{ °C}, I_F = 990 - 2970\text{ A}$	$V_{TO}$	-	-	1,00	
On-state slope resistance, $T_j = 175\text{ °C}, I_F = 990 - 2970\text{ A}$	$r_T$	-	-	0,4	mΩ
Recovery charge, $T_j = 175\text{ °C}, I_F = 630\text{ A}, di_F/dt = -5\text{ A}/\mu\text{s}, V_R \geq 100\text{ V}$	$Q_{RR}$	-	-		μAs
Recovery current, $T_j = 175\text{ °C}, I_F = 630\text{ A}, di_F/dt = -5\text{ A}/\mu\text{s}, V_R \geq 100\text{ V}$	$I_{RR}$	-	-		A
<b>THERMAL PARAMETERS</b>					
Thermal resistance junction to case, DC per diode cathode side cooled	$R_{th(j-c)}$	-	-	0,06	°C/W
<b>MECHANICAL PARAMETERS</b>					
Weight	w	-	0,58	-	kg
Torque	Md	13	-	17	N·m
Centrifugal the acceleration, working along an axis of symmetry of the diode aside the bases: Long Short-term(5min)	a			47088 66708	m/c <sup>2</sup>
Long tangential the acceleration, working perpendiculary axes of the diode				4900	



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**Fig. 1. Device Outline Drawing**  
(dimensions in mm)



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